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PTO-1449 (MPEP 609) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT	ATTY. DOCKET NO. <b>211.001-D3-US</b>	SERIAL NUMBER <b>10/724,648</b>
	APPLICANT(S) <b>Fazan et al.</b>	
	FILING DATE <b>December 1, 2003</b>	GROUP ART UNIT

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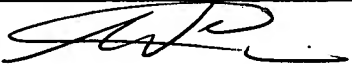
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WSL	4,032,947	6/1977	Kesel et al.			
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	3,439,214	4/1969	Kabell			
	6,081,443	6/2000	Morishita			
	6,111,778	8/2000	MacDonald et al.			

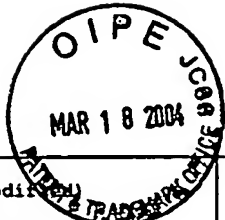
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WSL	FR 2 197 494	3/1974	French			
	EP 1 180 799	2/2002	European			
	EP 0 030 856	6/1981	European			
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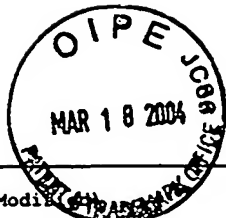
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USL	5,936,265	8/1999	Koga			
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WBL	EP 0 801 427	10/1997	European			
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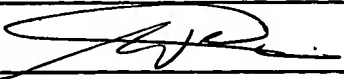
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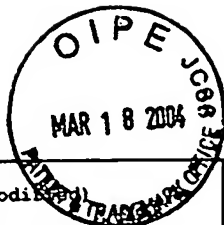
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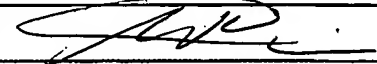
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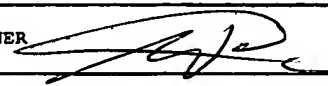
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WSL	4,979,014	12/1990	Hieda et al.			
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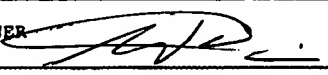
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WSL	5,886,385	3/1999	Arisumi et al.			
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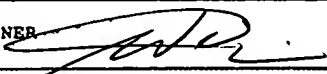
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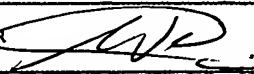
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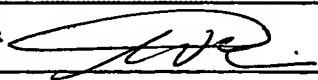
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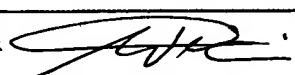
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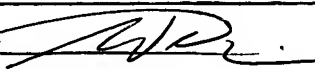
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WSL	6,297,090	10/2001	Kim			
↓	6,384,445	5/2002	Hidaka et al.			
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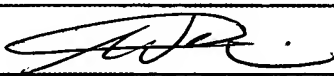
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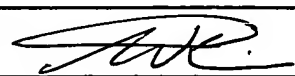
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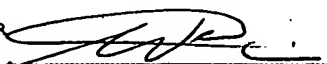
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